ABSTRACT OF THE DISCLOSURE

The present invention relates to a flat panel display device comprising a polycrystalline silicon thin film transistor and provides a flat panel display device having improved characteristics by having a different number of grain boundaries included in polycrystalline silicon thin film formed in active channel regions of a driving circuit portion and active channel regions of pixel portion. This may be achieved by having a different number of grain boundaries included in the polycrystalline silicon thin film formed in active channel regions of a switching thin film transistor and a driving thin film transistor formed in the pixel portion, and by having a different number of grain boundaries included in polycrystalline silicon thin film formed in active channel regions of a thin film transistor for driving the pixel portion for each red, green and blue of the pixel portion. Further, this may be achieved by having a different number of grain boundaries included in polycrystalline silicon formed in active channel regions of an NMOS thin film transistor and a PMOS thin film transistor for forming CMOS transistor used in flat panel display device, thereby constructing a thin film transistor to obtain the improved characteristics for each transistor.